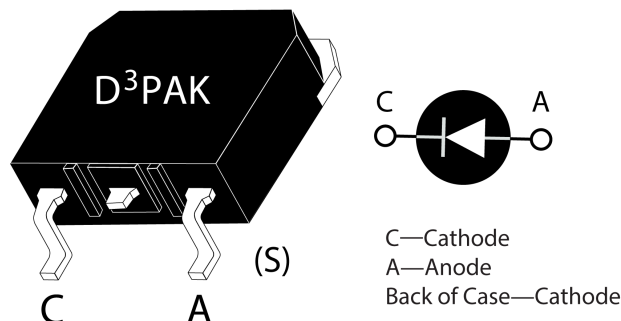


MSC0 5 0 SDA1 2 0 S Zero Recovery Silicon Carbide Schottky Diode

1 Product Overview



1.1 Features

The following are key features of the MSC0 5 0 SDA1 2 0 S device:

- Low forward voltage
- Low leakage current
- No reverse recovery current/no forward recovery
- Avalanche energy rated
- RoHS compliant

1.2 Benefits

The following are benefits of the MSC0 5 0 SDA1 2 0 S device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

1.3 Applications

The MSC0 5 0 SDA1 2 0 S device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
 - Switch-mode power supply
 - Inverters/converters
 - Motor controllers
- Freewheeling diode
 - Switch-mode power supply
 - Inverters/converters
- Snubber/clamp diode

2 Device Specifications

This section details the specifications for the MSC0 5 0 SDA1 2 0 S device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC0 5 0 SDA1 2 0 S device. All ratings are at $T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit	
V_R	Maximum DC reverse voltage	1 2 0 0	V	
V_{RRM}	Maximum peak repetitive reverse voltage			
V_{RWM}	Maximum working peak reverse voltage			
I_F	Maximum DC forward current	$T_c = 25\text{ }^\circ\text{C}$	1 0 9	A
		$T_c = 135\text{ }^\circ\text{C}$	4 9	
		$T_c = 145\text{ }^\circ\text{C}$	4 1	
I_{FRM}	Repetitive peak forward surge current ($T_c = 25\text{ }^\circ\text{C}$, $t = 8.3\text{ ms}$, half sine wave)	1 5 4		
I_{FSM}	Non-repetitive forward surge current ($T_c = 25\text{ }^\circ\text{C}$, $t = 8.3\text{ ms}$, half sine wave)	2 9 0		
P_{tot}	Power dissipation	$T_c = 25\text{ }^\circ\text{C}$	4 2 9	W
		$T_c = 110\text{ }^\circ\text{C}$	1 8 6	
T_J, T_{STG}	Operating junction and storage temperature range	-5 5 to 1 7 5	$^\circ\text{C}$	
T_L	Lead temperature for 1 0 seconds	3 0 0		
E_{AS}	Single-pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $L = 0.08\text{ mH}$, peak $I_L = 5.0\text{ A}$)	1 0 0	mJ	

The following table shows the thermal and mechanical characteristics of the MSC0 5 0 SDA1 2 0 S Dev

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0 .2 4	0 .3 5	$^\circ\text{C}/\text{W}$
Wt	Package weight		0 .1 4		oz
			3 .9		g

2.2 Electrical Performance

The following table shows the static characteristics of the MSC0 5 0 SDA1 2 0 S device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Forward voltage	$I_F = 50 \text{ mA}, T = 25 \text{ }^\circ\text{C}$		1.5	1.8	V
		$I_F = 50 \text{ mA}, T = 75 \text{ }^\circ\text{C}$		2.1		
I_{RM}	Reverse leakage current	$V_R = 1200 \text{ V}, T = 25 \text{ }^\circ\text{C}$		1.5	200	μA
		$V_R = 1200 \text{ V}, T = 75 \text{ }^\circ\text{C}$		250		
Q_C	Total capacitive charge	$V_R = 600 \text{ V}, T = 25 \text{ }^\circ\text{C}$		2.24		nC
C_j	Junction capacitance	$V_R = 400 \text{ V}, T = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$		2.46		pF
	Junction capacitance	$V_R = 800 \text{ V}, T = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$		1.82		

2.3 Performance Curves

This section shows the typical performance curves for the MSC0 5 0 SDA1 2 0 S device.

Figure 1 • Maximum Transient Thermal Impedance

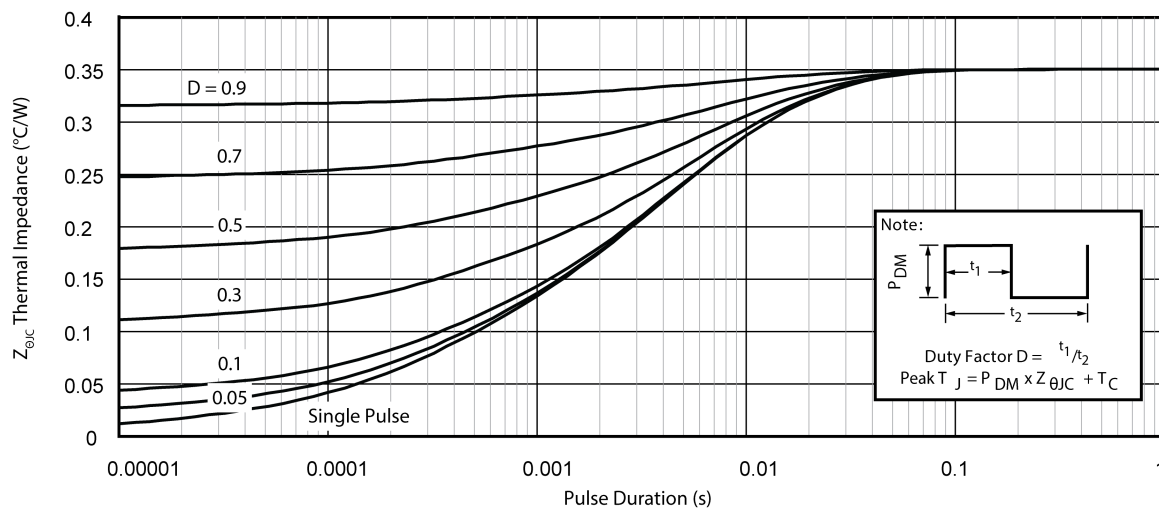


Figure 2 • Forward Current vs. Forward Voltage

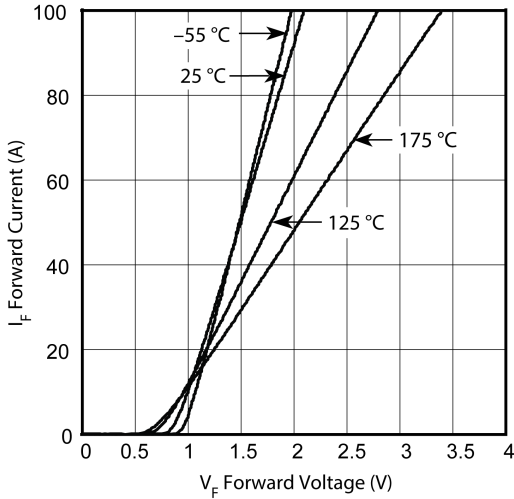


Figure 3 • Max Forward Current vs. Case Temp

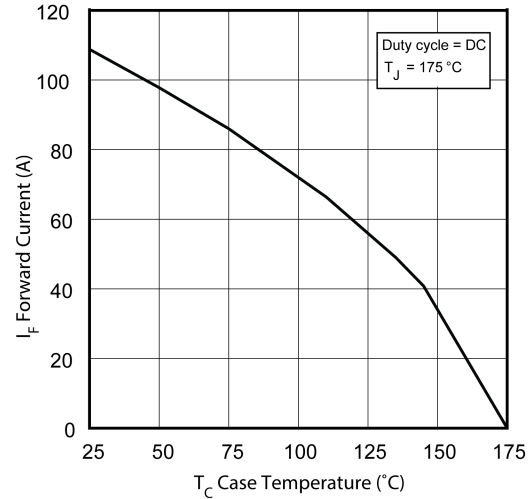


Figure 4 • Max Power Dissipation vs. Case Temp

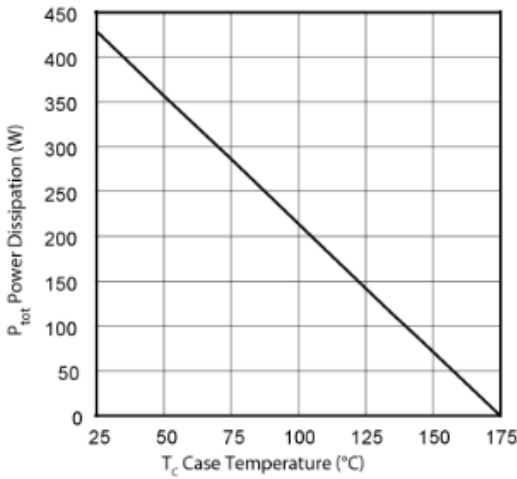


Figure 5 • Reverse Current vs. Reverse Voltage

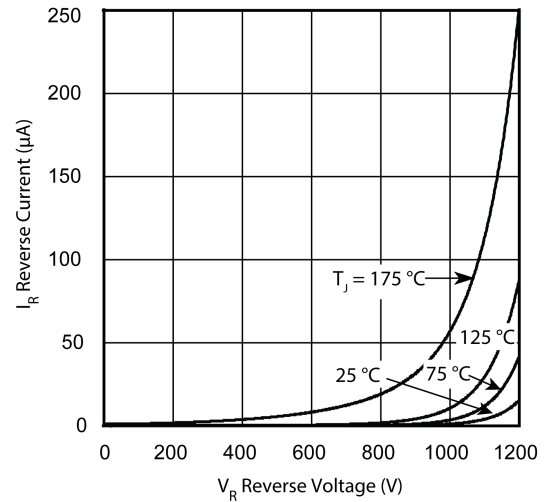


Figure 6 • Total Capacitive Charge vs. Reverse Voltage

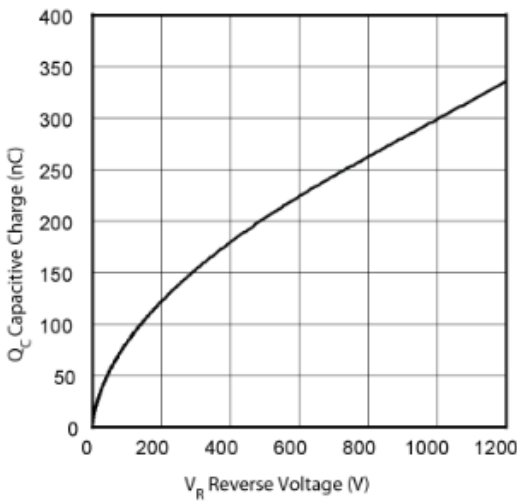
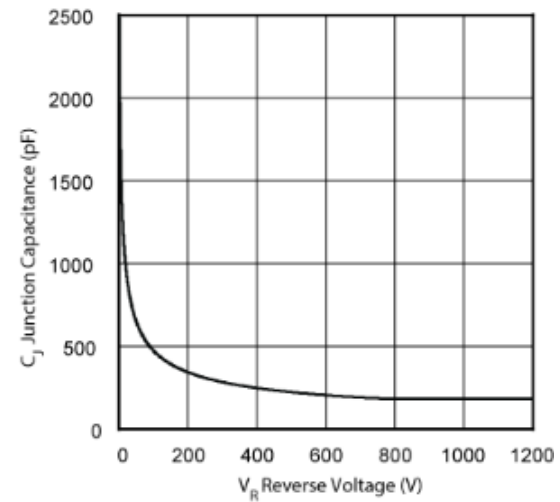


Figure 7 • Junction Capacitance vs. Reverse Voltage



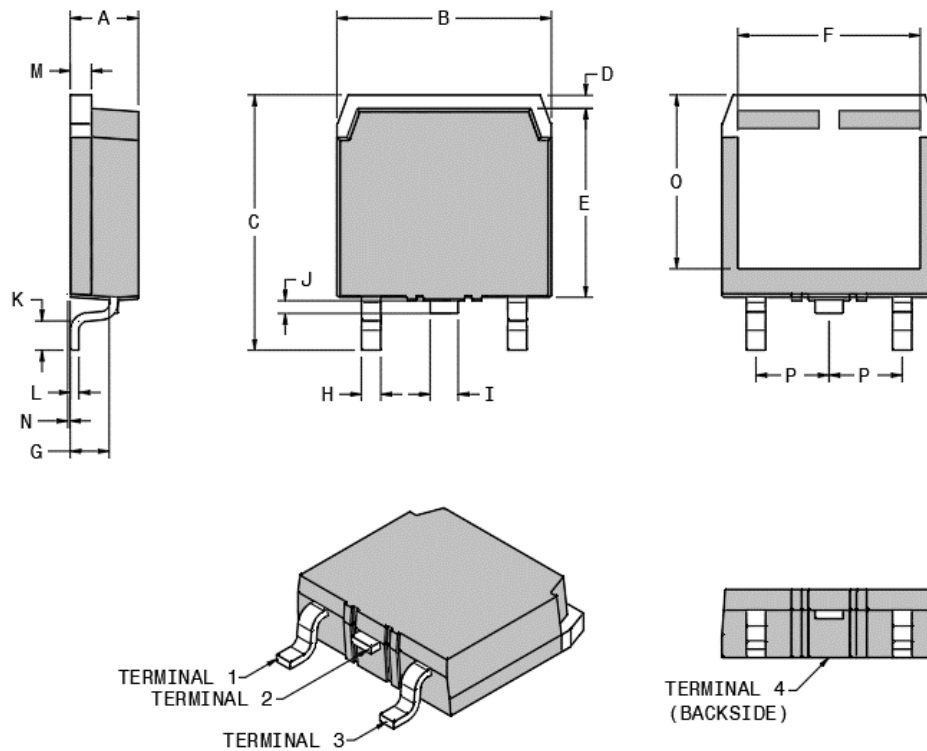
3 Package Specification

This section outlines the package specification for the MSC0 5 0 SDA1 2 0 S device.

3.1 Package Outline Drawing

This section shows the TO-2 6 8 package drawing of the MSC0 5 0 SDA1 2 0 S device.

Figure 8 • Package Outline Drawing



The following table lists the TO-2 6 8 dimensions and should be used in conjunction with the Package Outline Drawing.

Table 4 • TO-2 6 8 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.90	5.10	0.193	0.201
B	15.85	16.20	0.624	0.638
C	18.70	19.10	0.736	0.752
D	1.00	1.25	0.039	0.049
E	13.80	14.00	0.543	0.551
F	13.30	13.60	0.524	0.535
G	2.70	2.90	0.106	0.114
H	1.15	1.45	0.045	0.057
I	1.95	2.21	0.077	0.087
J	0.94	1.40	0.037	0.055

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
K	2.40	2.70	0.094	0.106
L	0.40	0.60	0.016	0.024
M	1.45	1.60	0.057	0.063
N	0.00	0.18	0.000	0.007
O	12.40	12.70	0.488	0.500
P	5.45 BSC (nom.)		0.215 BSC (nom.)	
Terminal 1	Cathode			
Terminal 2	Cathode			
Terminal 3	Anode			
Terminal 4	Cathode			



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